



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE5555 & NTE5557 Silicon Controlled Rectifier (SCR) 820 Amp, TO200AB

Absolute Maximum Ratings: ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Repetitive Peak Voltages, V_{RRM} , V_{DRM} , V_{DSM}	
NTE5555	600V
NTE5557	1600V
Non-Repetitive Peak Reverse Blocking Voltage, V_{RSM}	
NTE5555	700V
NTE5557	1700V
Average On-State Current (Half Sine Wave), $I_{T(AV)}$	
$T_{hs} = +55^\circ\text{C}$ (Double Side Cooled)	735A
$T_{hs} = +85^\circ\text{C}$ (Single Side Cooled)	290A
RMS On-State Current ($T_{hs} = +25^\circ\text{C}$, Double Side Cooled), $I_{T(RMS)}$	
1470A	
Continuous On-State Current ($T_{hs} = +25^\circ\text{C}$, Double Side Cooled), I_T	
1230A	
Peak One-Cycle Surge (10ms duration, 60% V_{RRM} re-applied), I_{TSM} (1)	
7600A	
Non-Repetitive On-State Current (10ms duration, $V_R \leq 10V$), I_{TSM} (2)	
8360A	
Maximum Permissible Surge Energy ($V_R \leq 10V$), I^2t	
10ms duration	349000A ² s
3ms duration	256000A ² s
Peak Forward Gate Current (Anode positive with respect to cathode), I_{FGM}	
20A	
Peak Forward Gate Voltage (Anode positive with respect to cathode), V_{FGM}	
18V	
Peak Reverse Gate Voltage, V_{RGM}	
5V	
Average Gate Power, P_G	
2W	
Peak Gate Power (100 μ s pulse width), P_{GM}	
100W	
Rate of Rise of Off-State Voltage (To 80% V_{DRM} gate open-circuit), dv/dt	
200V/ μ s	
Rate of Rise of On-State Current, di/dt	
(Gate drive 20V, 20 Ω with $t_r \leq 1\mu$ s, anode voltage $\leq 80\%$ V_{DRM})	
Repetitive	500A/ μ s
Non-Repetitive	1000A/ μ s
Operating Temperature Range, T_{hs}	
-40° to +125°C	
Storage Temperature Range, T_{stg}	
-40° to +150°C	
Thermal Resistance, Junction-to-Heatsink, $R_{th(j-hs)}$	
(For a device with a maximum forward voltage drop characteristic)	
Double Side Cooled	0.05°C/W
Single Side Cooled	0.1°C/W

Absolute Maximum Ratings (Cont'd): ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Peak On-State Voltage ($I_{TM} = 1550\text{A}$), V_{TM}	1.78V
Forward Conduction Threshold Voltage, V_O	1.03V
Forward Conduction Slope Resistance, r	0.483m Ω
Repetitive Peak Off-State Current (At V_{DRM}), I_{DRM}	40mA
Repetitive Peak Reverse Current (At V_{RRM}), I_{RRM}	40mA
Maximum Gate Current ($V_A = 6\text{V}$, $I_A = 1\text{A}$, $T_J = +25^\circ\text{C}$), I_{GT}	150mA
Maximum Gate Voltage ($V_A = 6\text{V}$, $I_A = 1\text{A}$, $T_J = +25^\circ\text{C}$), V_{GT}	3V
Maximum Holding Current ($V_A = 6\text{V}$, $I_A = 1\text{A}$, $T_J = +25^\circ\text{C}$), I_H	500mA
Maximum Gate Voltage Which Will Not Trigger Any Device, V_{GD}	0.25V

